



FORM PTO 449 APR 26 2004 PATENT & TRADEMARK OFFICE	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX 448A	APPLICATION NO. 10/800,390
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Brabant et al.	
		FILING DATE March 12, 2004	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	US 2003/0157787	08/21/03	Murthy et al.			
DV	2	US 2003/0207127	11/06/03	Murthy et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						

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EXAMINER <i>Shuland</i>	DATE CONSIDERED <i>09/03/05</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 808; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Application No. 10/800,390  
 Filing Date March 12, 2004  
 First Named Inventor Paul D. Brabant  
 Art Unit 2818  
 Examiner David Vu  
 Attorney Docket No. ASMEX.448A

(Multiple sheets used when necessary)

APR 25 2005

SHEET 1 OF 1

## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DV	1	2003/0045063	03/06/2003	Oda	_____
DV	2	2003/0082300	05/01/2003	Todd et al.	_____
DV	3	2003/0124818	07/03/2003	Luo et al.	_____
DV	4	2005/0079892	04/14/2005	Samoilov et al.	_____

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>1</sup>
DV	5	WO 00/15885	03/23/2000	Hernandez et al.	_____	

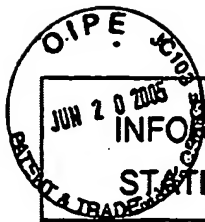
## NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
DV	6	International Search Report for International Application No. PCT/US04/07564 dated April 6, 2005.	

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Examiner Signature <i>Shuland</i>	Date Considered 03/03/05
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PTO/SB/08 Equivalent

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Multiple sheets used when necessary)  SHEET 1 OF 1	Application No.	10/800,390
	Filing Date	March 12, 2004
	First Named Inventor	Paul D. Brabant
	Art Unit	2818
	Examiner	David Vu
	Attorney Docket No.	ASMEX.448A

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DV	1.	2005/0079892	04/14/2005	Samoilov et al.	—

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Examiner Signature <i>Philant</i>	Date Considered 09/03/05
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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMEX 448AAPPLICATION NO.  
10/800,390INFORMATION DISCLOSURE STATEMENT  
BY APPLICANTAPPLICANT  
Brabant et al.FILING DATE  
March 12, 2004GROUP  
Unknown

(USE SEVERAL SHEETS IF NECESSARY)

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	US 2003/0235931 A1	12/25/03	Wada et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
DV	2	Cannon, D. et al., "Tensile strained epitaxial Ge films on Si(100) substrates with potential application in L-band telecommunications," Applied Physics Letters, Volume 84, Number 6, February 9, 2004, pp. 906-908.					
	3	Colace, L. et al., "Efficient high-speed near-infrared Ge photodetectors integrated on Si substrates," Applied Physics Letters, Volume 76, Number 10, March 6, 2000, pp. 1231-1233.					
	4	Colace, L. et al., "Ge-on-Si Approaches to the Detection of Near-Infrared Light," IEEE Journal of Quantum Electronics, Vol. 35, No. 12, December 1999, pp. 1843-1852.					
	5	Fama, S. et al., "High performance germanium-on-silicon detectors for optical communications," Applied Physics Letters, Volume 81, Number 4, July 22, 2002, pp. 586-588.					
	6	Hull, R., "Metastable strained layer configurations in the SiGe/Si system," (1999) EMIS Datereviews, Series No. 24: Properties of SiGe and SiGe:C, edited by Erich Kasper et al., INSPEC (2000), London, UK					
	7	Ishikawa, Y. et al., "Strain-induced band gap shrinkage in Ge grown on Si substrate," Applied Physics Letters, Volume 82, Number 12, March 31, 2003, pp. 2044-2046.					
	8	Lee et al., "Growth of strained Si and strained Ge heterostructures on relaxed Si <sub>1-x</sub> G <sub>x</sub> by ultrahigh vacuum chemical vapor deposition," J. Vac. Sci. Technol. B 22(1) (Jan/Feb 2004).					
	9	Li, Q. et al., "Selective growth of Ge on Si(100) through vias of SiO <sub>2</sub> nanotemplate using solid source molecular beam epitaxy," Applied Physics Letters, Volume 83, Number 24, December 15, 2003, pp. 5032-5034.					
DV	10	Liu, J. et al., "Silicidation-induced band gap shrinkage in Ge epitaxial films on Si," Applied Physics Letters, Volume 84, Number 5, February 2, 2004, pp. 660-662.					

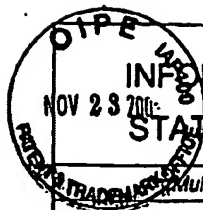
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Brabant

DATE CONSIDERED

05/03/05

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PTO/SB/08 Equivalent

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Multiple sheets used when necessary)

SHEET 1 OF 4

Application No.	10/800,390
Filing Date	12 March 2004
First Named Inventor	Paul D. Brabant
Art Unit	2818
Examiner	David Vu
Attorney Docket No.	ASMEX.448A

## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DV	1	5,221,556	06/22/93	Hawkins et al.	—
	2	5,879,970	03/09/99	Shiota et al.	—
	3	6,093,252	07/25/00	Wengert et al.	—
	4	6,319,782	11/20/01	Nakabayashi	—
	5	6,373,112	04/16/02	Murthy et al.	—
	6	6,537,370	03/25/03	Hernandez et al.	—
	7	6,592,942	07/15/03	Van Wijck	—
	8	2002/0173130	11/21/02	Pomeroy et al.	—
	9	2003/0190791	10/09/03	Fischetti, et al.	—
	10	2003/0235931	12/25/03	Wada et al.	—
DV	11	2004/0219735	11/04/04	Brabant et al.	—

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DV	12	WO 01/41544	08/14/01	PCT		

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DV	13	BAUER et al., "Relaxed SiGe buffers with thicknesses below 0.1 $\mu\text{m}$ ", <i>Thin Solid Films</i> 369:152-156 (2000).	
DV	14	BAUER et al., "High Ge content photodetectors on thin SiGe buffers", <i>Materials Science and Engineering B</i> 89:77-83 (2002).	
DV	15	BENSAHEL et al., "Single-wafer processing of In-situ doped polycrystalline Si and Si <sub>1-x</sub> Ge <sub>x</sub> ", <i>Solid State Technology</i> , pages S5-S10 (March 1998).	

Examiner Signature <i>David Vu</i>	Date Considered 01/21/06
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PTO/SB/09 Equivalent

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	Filing Date	12 March 2004
	First Named Inventor	Paul D. Brabant
	Art Unit	2818
(Multiple sheets used when necessary)		Examiner
SHEET 1 OF 1		Attorney Docket No.
		ASMEEX.448A

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DV	1	5,256,550	10/1993	Laderman et al.	
	2	5,891,769	04/1999	Liaw et al.	
	3	6,030,884	02/2000	Hada et al.	
	4	6,573,126	06/2003	Cheng et al.	
	5	6,713,326	03/2004	Cheng et al.	
	6	6,844,213	01/2005	Sparks	
	7	6,858,502	02/2005	Chu et al.	
	8	6,900,115	05/31/05	Todd	
	9	6,562,738	05/13/03	Yanagawa et al.	
DV	10	2004/0217845	11/2004	Silver et al.	

FOREIGN PATENT DOCUMENTS						
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PTO/SB/08 Equivalent

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U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567.B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
DV	1	6958253	10/25/05	Todd	—
DV	2	2006/0216417	9/28/06	Todd et al.	—

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Examiner Signature <i>W. H. H. H.</i>	Date Considered 02/03/07
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